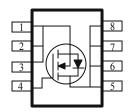
N-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY					
$V_{DS}(V)$	$r_{DS(on)} m(\Omega)$ $I_D(A)$				
20	$22@V_{CS}=4.5V$	9.7			
	$28@V_{CS}=2.5V$	8.6			

- Low r_{DS(on)} provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOIC-8 saves board space
- Fast switching speed
- High performance trench technology





ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C UNLESS OTHERWISE NOTED)						
Parameter Parameter		Symbol	Limit	Units		
Drain-Source Voltage			20	V		
Gate-Source Voltage			±8	v		
C t D · C a	T _A =25°C		±9.7			
Continuous Drain Current ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	1D	±8.0	Α		
Pulsed Drain Current ^b			±50			
Continuous Source Current (Diode Conduction) ^a			2.3	Α		
D D a	T _A =25°C	D	3.1	W		
Power Dissipation ^a	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	FD	2.2			
Operating Junction and Storage Temperature Range		T_{J}, T_{stg}	-55 to 150	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
M · T · · · · · · · · · · · · · · · · ·	t <= 10 sec	.D	50	°C/W	
Maximum Junction-to-Ambient ^a	Steady State	$R_{\theta JA}$	92	°C/W	

1

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Count of	Total Conditions	Limits			Unit	
rarameter	Symbol Test Conditions		Min	Тур	Max	Unit	
Static							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0 \text{ V}, I_D = 250 \text{ uA}$	20			V	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1.0			ľ	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±100	nA	
Zoro Coto Voltogo Droin Current		$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$			1 ,, 4		
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	uA	
On-State Drain Current ^A	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = \pm 12 \text{ V}$	20			A	
Dunin Grand On Braintan A	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 9.7 \text{ A}$			22		
Drain-Source On-Resistance ^A		$V_{GS} = 2.5 \text{ V}, I_D = 8.6 \text{ A}$			28	mΩ	
Forward Tranconductance ^A	\mathbf{g}_{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 9.7 \text{ A}$		40		S	
Diode Forward Voltage	V_{SD}	$I_S = 2.3 \text{ A}, V_{GS} = 0 \text{ V}$		0.7		V	
Dynamic ^b							
Total Gate Charge	Q_{g}	V = 15 V V = 45 V		5.5			
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$ $I_{D} = 9.7 \text{ A}$		1.0		nC	
Gate-Drain Charge	Q_{gd}	$I_{\rm D} = 9.7$ A		1.4		1	
Turn-On Delay Time	$t_{d(on)}$			20			
Rise Time	t _r	$V_{DD} = 25 \text{ V}, R_L = 25 \Omega, I_D = 1 \text{ A},$		9		nS	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}$		70		пъ	
Fall-Time	$t_{ m f}$			20		1	

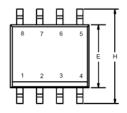
Notes

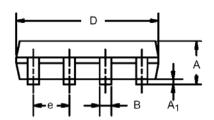
- a. Pulse test: $PW \le 300us duty cycle \le 2\%$.
- b. Guaranteed by design, not subject to production testing.

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Package Information

SO-8: 8LEAD





	MILLIN	IETERS	INC	CHES	
Dim	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27 BSC		0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	

